

STD15NF10

N-channel 100 V, 0.060 Ω, 23 A, DPAK low gate charge STripFET™ II Power MOSFET

Features

Туре	V _{DSSS}	R _{DS(on)} max	I _D
STD15NF10	100 V	< 0.065 Ω	23 A

- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Application

■ Switching applications

Description

This MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced highefficiency, high-frequency isolated DC-DC converters for telecom and computer applications. It is also intended for any applications with low gate drive requirements.

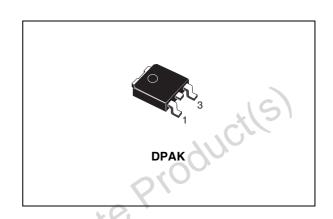


Figure 1. Internal schematic diagram

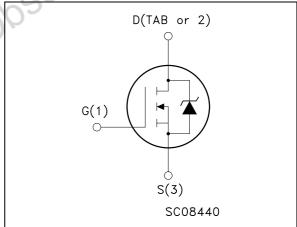


Table 1. Device summary

Order code	Marking	Package	Packaging
STD15NF10T4	D15NF10	DPAK	Tape and reel

Contents STD15NF10

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STD15NF10 Electrical ratings

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source voltage (V _{GS} = 0)	100	V
V _{DGR}	Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)	100	٧
V _{GS}	Gate-source voltage	± 20	V
I _D	Drain current (continuous) at $T_C = 25$ °C	23	Α
I _D	Drain current (continuous) at T _C =100 °C	16	Α
I _{DM} ⁽¹⁾	Drain current (pulsed)	92	Α
P _{TOT}	Total dissipation at $T_C = 25$ °C	70	W
	Derating factor	0.46	W/°C
E _{AS} (2)	Single pulse avalanche energy	180	mJ
dv/dt (3)	Peak diode recovery voltage slope	9	V/ns
T _{stg}	Storage temperature	-55 to 175	°C
T_J	Max. operating junction temperature	-55 15 175	

- 1. Pulse width limited by safe operating area
- 2. Starting $T_J = 25$ °C, $I_D = 10A$, $V_{DD} = 30V$
- 3. $I_{SD} \leq$ 13 A, di/dt \leq 300 A/ μ s, $V_{DS} \leq$ $V_{(BR)DSS}$, $T_{J} \leq$ T_{JMAX}

Table 3. Thermal data

	Symbol	Parameter	Value	Unit
	R _{thJC}	Thermal resistance junction-case max	2.14	°C/W
	R _{thJA}	Thermal resistance junction-ambient max	100	°C/W
0/6	Τ	Maximum lead temperature for soldering purpose	300	°C
Open				

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Electrical characteristics STD15NF10

Electrical characteristics 2

(T_{CASE} = 25 °C unless otherwise specified)

Table 4. On⁽¹⁾ /off states

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			٧
I _{DSS}	Zero gate voltage drain current (V _{GS} = 0)	V_{DS} = Max rating V_{DS} = Max rating,@ 125 °C			1	μA μA
I _{GSS}	Gate body leakage current (V _{DS} = 0)	V _{GS} = ± 20 V		(±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2	3	4	٧
R _{DS(on)}	Static drain-source on resistance	V _{GS} = 10 V, I _D = 12 A		0.06	0.065	Ω

^{1.} Pulsed: Pulse duration = 300 μs, duty cycle 1.5%

Table 5. **Dynamic**

nDS(on)	resistance	V _{GS} = 10 V, I _D = 12 A		0.06	0.065	2.2
1. Pulsed: Table 5.	Pulse duration = 300 μs, duty cyc Dynamic	le 1.5%				
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
g _{fs} ⁽¹⁾	Forward transconductance	$V_{DS} = 15 V_{,} I_{D} = 7.5 A$		12		S
C _{iss} C _{oss} C _{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V _{DS} = 25 V, f = 1 MHz, V _{GS} = 0		870 125 50		pF pF pF
Q _g Q _{gs} Q _{gd}	Total gate charge Gate-source charge Gate-drain charge	$V_{DD} = 80 \text{ V}, I_{D} = 24 \text{ A}$ $V_{GS} = 10 \text{ V}$		30 6 10	40	nC nC nC

^{1.} Pulsed: pulse duration=300µs, duty cycle 1.5%

Table 6. **Switching times**

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
$t_{ m d(on)}$ $t_{ m r}$ $t_{ m d(off)}$ $t_{ m f}$	Turn-on delay time Rise time Turn-off delay time Fall time	V_{DD} = 50 V, I_{D} = 12 A, R_{G} = 4.7 Ω , V_{GS} = 10 V Figure 13 on page 8		60 45 49 17		ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Тур.	Max	Unit
I _{SD}	Source-drain current				23	Α
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)				92	Α
V _{SD} ⁽²⁾	Forward on voltage	I _{SD} = 20 A, V _{GS} = 0			1.5	V
t _{rr} Q _{rr} I _{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current oth limited by safe operating area. oulse duration = 300 µs, duty cycle	I_{SD} = 24 A, di/dt = 100 A/ μ s, V_{DD} = 30 V, T_{J} = 150 °C Figure 15 on page 8		100 375 7.5		ns nC A
Pulse wi	dth limited by safe operating area.	<u> </u>			119	5)
2. Pulsed: ¡	oulse duration = 300 μs, duty cycle	1.5%		(
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Electrical characteristics STD15NF10

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Thermal impedance

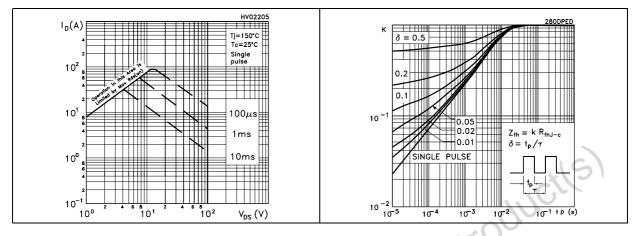


Figure 4. Output characteristics

Figure 5. Transfer characteristics

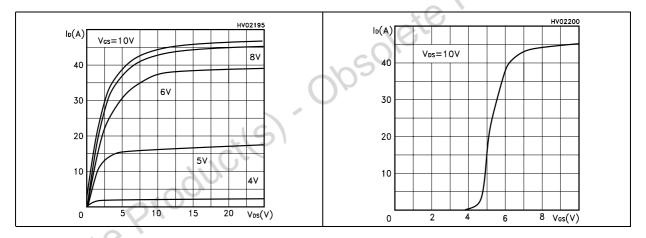
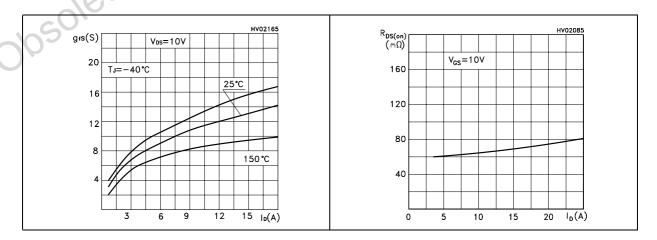


Figure 6. Transconductance

Figure 7. Static drain-source on resistance



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Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations

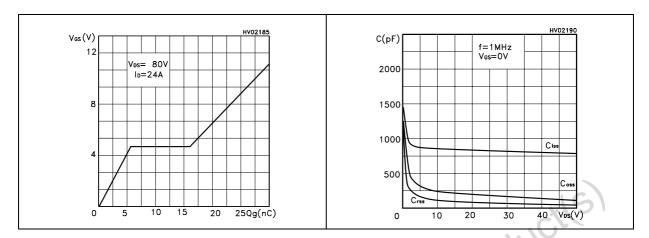


Figure 10. Normalized gate threshold voltage Figure 11. Normalized on resistance vs. vs. temperature temperature

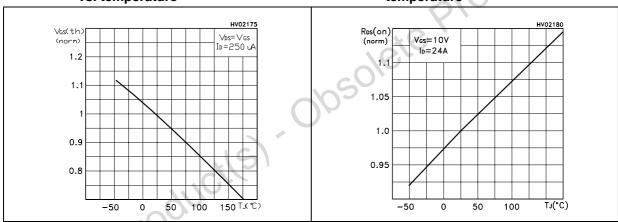
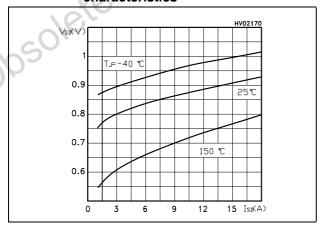


Figure 12. Source-drain diode forward characteristics



Test circuit STD15NF10

3 Test circuit

Figure 13. Switching times test circuit for resistive load

Figure 14. Gate charge test circuit

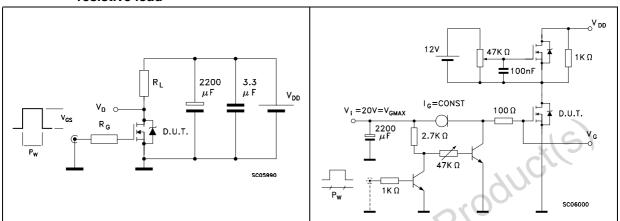


Figure 15. Test circuit for inductive load switching and diode recovery times

Figure 16. Unclamped Inductive load test circuit

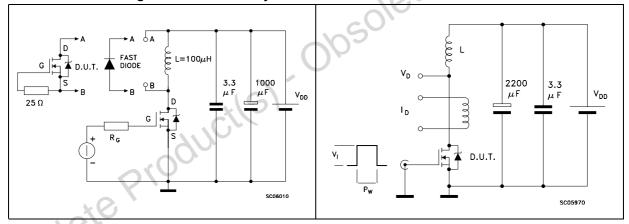
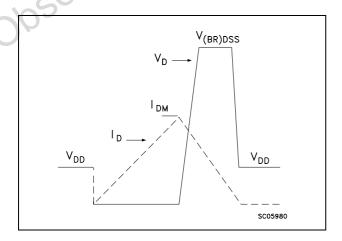


Figure 17. Unclamped inductive waveform



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4 Package mechanical data

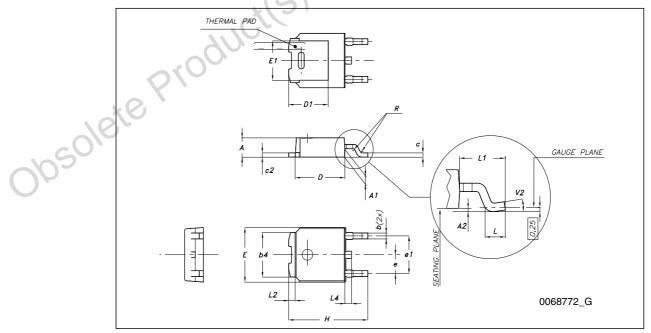
In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

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Obsolete Product(s).

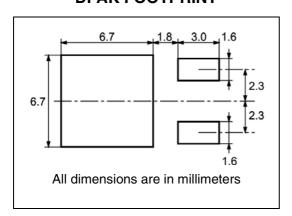
TO-252 (DPAK) mechanical data

DIM.		mm.	
DIIVI.	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	7//
E	6.40		6.60
E1		4.70	
е		2.28	
e1	4.40	.0.	4.60
Н	9.35	10	10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0 °		8 °

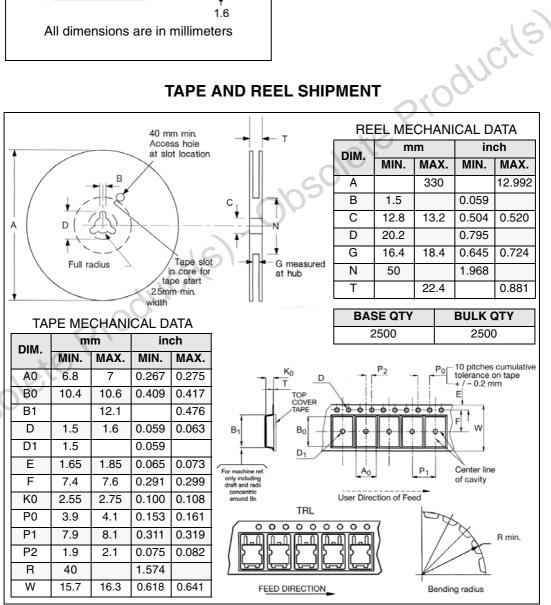


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Packaging mechanical data 5 **DPAK FOOTPRINT**



TAPE AND REEL SHIPMENT



Revision history STD15NF10

6 Revision history

Table 8. Revision history

Date
21-Jun-2004
09-Sep-2004
08-Aug-2006
04-Nov-2008
08-Aug-2006 04-Nov-2008

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